

30V N-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

BV _{DSS}	R _{DS(ON)} MAX	I _{D MAX} T _A = +25°C
30V	17mΩ @ V _{GS} = 10V	8.4A
30 V	28mΩ @ V _{GS} = 4.5V	6.8A

Features

- 0.6mm Profile Ideal for Low Profile Applications
- PCB Footprint of 4mm²
- Low Gate Threshold Voltage
- Low On-Resistance
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- The DMT3020LFDFQ is suitable for automotive applications requiring specific change control; this part is AEC-Q101 qualified, PPAP capable, and manufactured in IATF 16949 certified facilities.

https://www.diodes.com/quality/product-definitions/

Description and Applications

This MOSFET is designed to meet the stringent requirements of automotive applications. It is qualified to AEC-Q101, supported by a PPAP and is ideal for use in:

- Power Management Functions
- General Purpose Interfacing Switch

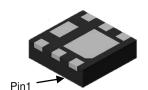
Mechanical Data

- Case: U-DFN2020-6
- Case Material: Molded Plastic, "Green" Molding Compound.
 UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish NiPdAu over Copper Leadframe. Solderable per MIL-STD-202, Method 208
- Weight: 0.0065 grams (Approximate)

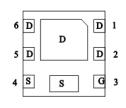
U-DFN2020-6 (Type F)



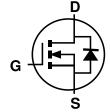
Top View



Bottom View



Pin Out Bottom View



Equivalent Circuit

Ordering Information (Note 4)

Part Number	Case	Packaging
DMT3020LFDFQ-7	U-DFN2020-6 (Type F)	3,000/Tape & Reel
DMT3020LFDFQ-13	U-DFN2020-6 (Type F)	10,000/Tape & Reel

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/



Marking Information

Site1

U-DFN2020-6 (Type F)



J6 = Product Type Marking Code YM = Date Code Marking Y = Year (ex: H = 2020) M = Month (ex: 9 = September)

Date Code Key

Date Code Ney												
Year	2020	2021	2022	2023	2024	2025	2026	2027	2028	2029	2030	2031
Code	Н		J	K	L	М	N	0	Р	R	S	Т
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	4		_	4	_	^	7				N.I.	

Site 2



J6 = Product Type Marking Code YWX = Date Code Marking Y = Year (ex: 0 = 2020)

W = Week (ex: a = Week 27; z Represents Week 52 and 53)

X = Internal Code (ex: U = Monday)

Date Code Key

Year	2020	2021	2022	2023	2024	2025	2026	2027	2028	2029	2030	2031
Code	0	1	2	3	4	5	6	7	8	9	0	1

Week	1-26	27-52	53
Code	A-Z	a-z	Z

Internal Code	Sun	Mon	Tue	Wed	Thu	Fri	Sat
Code	Т	U	V	W	X	Υ	Z



Maximum Ratings (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit		
Drain-Source Voltage			V_{DSS}	30	V
Gate-Source Voltage			Vgss	±20	V
Continuous Drain Current (Note 6) V _{GS} = 10.0V	Steady State	$T_A = +25$ °C $T_A = +70$ °C	ΙD	8.4 6.7	Α
Continuous Drain Current (Note 6) Vgs = 4.5V	Steady State	$T_A = +25$ °C $T_A = +70$ °C	lo	6.8 5.4	Α
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)		I _{DM}	40	Α
Maximum Body Diode Continuous Current (Note 6)	Is	2	Α		
Avalanche Current (Note 7) L = 0.1mH	I _{AS}	11.4	Α		
Avalanche Energy (Note 7) L = 0.1mH			Eas	6.5	mJ

Thermal Characteristics

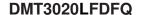
Characteristic		Symbol	Value	Unit	
Total Bower Dissipation (Note 5)	T _A = +25°C	D-	0.7	W	
Total Power Dissipation (Note 5)	T _A = +70°C	P_{D}	0.4	l vv	
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	Reja	180	°C/W	
Total Bayer Dissipation (Note 6)	T _A = +25°C	D-	1.8	W	
Total Power Dissipation (Note 6)	$T_A = +70^{\circ}C$	PD	1.1	VV	
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	Reja	70	°C/W	
Operating and Storage Temperature Range		TJ, TSTG	-55 to +150	°C	

Electrical Characteristics (@TA = +25°C, unless otherwise specified.)

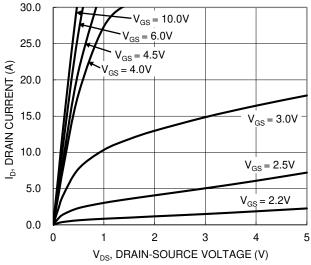
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 8)							
Drain-Source Breakdown Voltage	BV _{DSS}	30.0	_		V	$V_{GS} = 0V, I_D = 250\mu A$	
Zero Gate Voltage Drain Current T _J = +25°C	IDSS	_		1.0	μΑ	$V_{DS} = 24V$, $V_{GS} = 0V$	
Gate-Source Leakage	Igss	_	_	±100	nA	$V_{GS} = \pm 20V$, $V_{DS} = 0V$	
ON CHARACTERISTICS (Note 8)							
Gate Threshold Voltage	V _{GS(TH)}	1.0	-	2.5	٧	$V_{DS} = V_{GS}$, $I_D = 250\mu A$	
Static Drain-Source On-Resistance	Process		13	17	mΩ	$V_{GS} = 10V, I_D = 9.0A$	
Static Drain-Source On-Resistance	R _{DS(ON)}	_	21	28	11122	$V_{GS} = 4.5V, I_D = 7.0A$	
Diode Forward Voltage	V _{SD}	_	_	1.2	V	$V_{GS} = 0V, I_{S} = 2A$	
DYNAMIC CHARACTERISTICS (Note 9)							
Input Capacitance	Ciss	_	393	_	рF	V 45V V 0V	
Output Capacitance	Coss	_	173	_	рF	V _{DS} = 15V, V _{GS} = 0V, - f = 1.0MHz	
Reverse Transfer Capacitance	Crss	_	27	_	рF	T = T.OWITIZ	
Gate Resistance	Rg	_	1.1	_	Ω	$V_{DS} = 0V, V_{GS} = 0V, f = 1.0MHz$	
Total Gate Charge (V _{GS} = 10V)	Qg	_	7.0	_	nC		
Total Gate Charge (VGS = 4.5V)	Qg	_	3.6		nC	\/ 15\/ I- 04	
Gate-Source Charge	Qgs	_	0.9		nC	$V_{DD} = 15V, I_D = 9A$	
Gate-Drain Charge	Qgd	_	1.5	_	nC	1	
Turn-On Delay Time	td(ON)	_	1.8	_	ns		
Turn-On Rise Time	tR	_	1.9	_	ns	V _{DD} = 15V, V _{GS} = 10V,	
Turn-Off Delay Time	tD(OFF)	_	7.5	_	ns	$R_g = 6\Omega$, $I_D = 9A$	
Turn-Off Fall Time	t _F	_	2.4	_	ns	7	
Reverse Recovery Time	trr	_	10	_	ns	1 04 -11/-14 1004/	
Reverse Recovery Charge	Qrr	_	2.6	_	nC	I _F = 9A, dI/dt = 100A/μs	

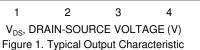
5. Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.

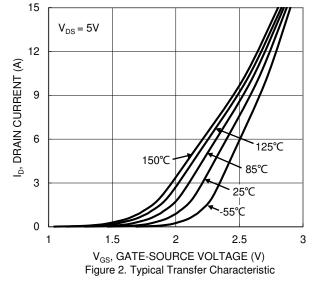
- 6. Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate.
- 7. I_{AS} and E_{AS} ratings are based on low frequency and duty cycles to keep $T_{J} = +25^{\circ}C$.
- Short duration pulse test used to minimize self-heating effect.
 Guaranteed by design. Not subject to product testing.











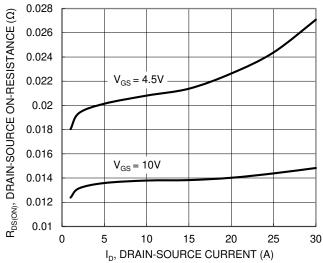


Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage

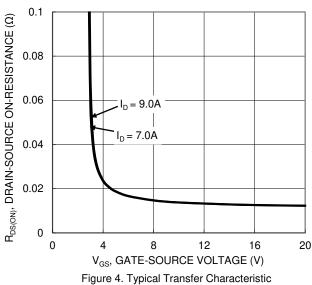
150°C

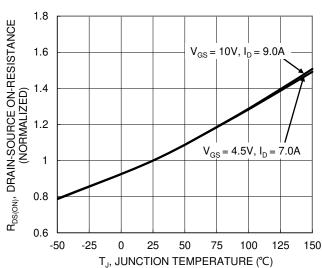
125°C

85°C

25°C

 $V_{GS} = 10V$





-55°C 5 15 20 0 10 25 30 I_D, DRAIN CURRENT (A) Figure 5. Typical On-Resistance vs. Drain Current and Junction Temperature

Figure 6. On-Resistance Variation with Junction Temperature

0.024

0.022

0.02

0.018

0.016

0.014

0.012

0.01

0.008

 $R_{DS(ON)}$, DRAIN-SOURCE ON-RESISTANCE (Ω)



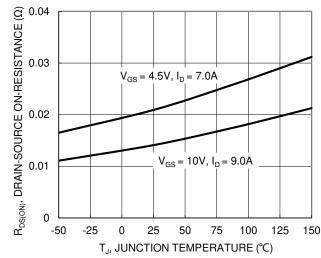
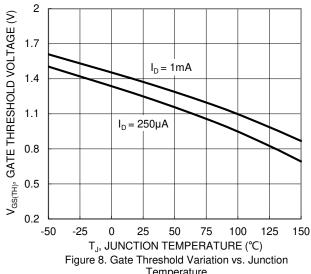
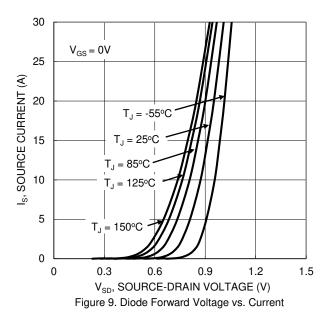


Figure 7. On-Resistance Variation with Junction Temperature



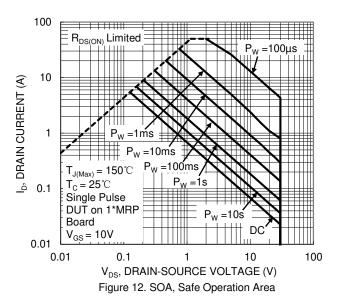
Temperature



10 8 6 $V_{GS}(V)$ 4 $V_{DS} = 15V, I_{D} = 9A$ 2 0 2 8 6 Q_g (nC)

Figure 11. Gate Charge

1000 f=1MHz C_{iss} C_T, JUNCTION CAPACITANCE (pF) $\mathsf{C}_{\mathsf{oss}}$ 100 C_{rss} 10 0 5 10 15 20 25 30 V_{DS} , DRAIN-SOURCE VOLTAGE (V) Figure 10. Typical Junction Capacitance





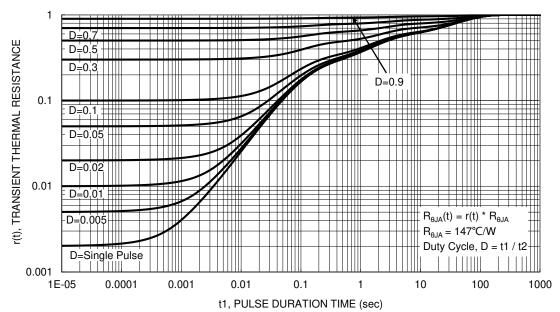


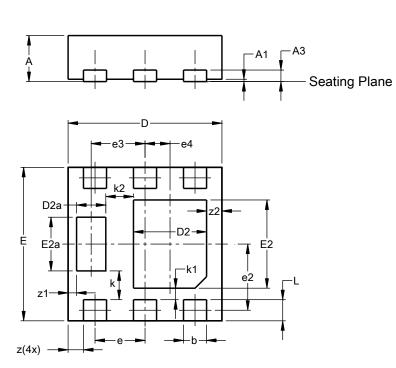
Figure 13. Transient Thermal Resistance



Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

U-DFN2020-6 (Type F)

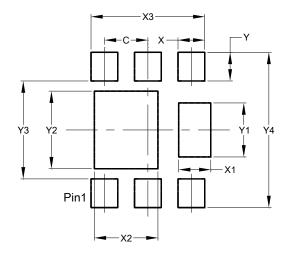


	U-DFN2020-6						
Dim	(Type F) Min Max Typ						
A	0.57	0.63	0.60				
A1	0.00	0.05	0.03				
A3	-	-	0.15				
b	0.25	0.35	0.30				
D	1.95	2.05	2.00				
D2	0.85	1.05	0.95				
D2a	0.33	0.43	0.38				
Е	1.95	2.05	2.00				
E2	1.05	1.25	1.15				
E2a	0.65	0.75	0.70				
е	_	0.65 BS	С				
e2	C	.863 BS	SC				
е3	(0.70 BS	С				
e4		.325 BS					
k		0.37 BS					
k1	(0.15 BS	С				
k2	(0.36 BS	С				
L		0.325					
Z	0.20 BSC						
z1	C	.110 BS	SC				
z2		0.20 BS	•				
All D	imens	ions in	mm				

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

U-DFN2020-6 (Type F)



Dimensions	Value (in mm)
С	0.650
X	0.400
X1	0.480
X2	0.950
Х3	1.700
Υ	0.425
Y1	0.800
Y2	1.150
Y3	1.450
Y4	2.300



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